

## ABSTRACT

A compound semiconductor light-emitting diode comprising  
a light-emitting layer composed of a Group III-V compound  
5 semiconductor, and a current diffusion layer provided on the  
light-emitting layer and composed of a Group III-V compound  
semiconductor, characterized in that the current diffusion  
layer is composed of a conductive boron-phosphide-based  
semiconductor and has a bandgap at room temperature wider  
10 than that of the light-emitting layer.